Abstracts

A single supply very high power and efficiency integrated PHEMT amplifier for GSM applications

F. Huin, C. Duvanaud, V. Serru, F. Robin and E. Leclerc. "A single supply very high power and efficiency integrated PHEMT amplifier for GSM applications." 2000 Radio Frequency Integrated Circuits (RFIC) Symposium 00. (2000 [RFIC]): 101-104.

The power PHEMT technology presented allows one to achieve high power (35.5 dBm) and PAE (60%) for a low drain bias of 3.5 volts and a gate bias of zero volts. For such operating conditions, analyses are conducted to adjust the load termination at the signal harmonics.

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